

REMARKS

Favorable reconsideration of this application as presently amended and in light of the following discussion is respectfully requested.

Claims 1, 3 and 4 are pending in the present application. Claims 2 and 5-28 are canceled without prejudice and Claims 1, 3 and 4 are amended by the present amendment.

In the outstanding Office Action, Claim 2 was rejected under 35 U.S.C. § 112, second paragraph; and Claims 1-5 were rejected under 35 U.S.C. § 103(a) as unpatentable over Applicants' Admitted Prior Art (AAPA) in view of Hong et al.

Regarding the rejection of Claim 2 under 35 U.S.C. § 112, second paragraph, Claim 2 is canceled. However, subject matter similar to that as recited in Claim 2 has been included in independent Claims 1, 3 and 4, and has been drafted in light of the comments noted in the outstanding Office Action. Accordingly, it is respectfully requested this rejection be withdrawn.

Claims 1-5 were rejected under 35 U.S.C. § 103(a) as unpatentable over AAPA in view of Hong et al. This rejection is respectfully traversed.

Claim 1 is amended to include similar features as Claim 2 and is directed to a thin film transistor array substrate in which a part of a semiconductor pattern surrounding a source electrode exists only on a first metallic pattern at a source electrode part in a pixel region. Independent Claims 3 and 4 include similar features.

In a non-limiting example, Figures 31(a)-31(d) and 73 show that the semiconductor region 230 is included in the gate line region at least in the source electrode region in both a source and part of a drain electrode region so that a part of the semiconductor region 230 surrounding the source electrode exists only on the gate line (electrode).

As an advantage, the gate electrode shields the light exposed from the back side of the gate electrode to the semiconductor region 230, thus preventing leakage current due to the light (see the specification at page 50, lines 8-14).

In contrast, Hong et al only discusses conductive patterns 71-76 that include portions on a drain electrode 66 in pixel areas. Figure 4 of Hong et al shows that a source electrode 65 and drain electrode 66 exist both over a gate electrode 26 and also in a region extending past the gate electrode. Therefore, Hong et al does not teach or suggest that a part of a semiconductor pattern surrounding a source electrode exists only on a metallic pattern, as in the independent claims.

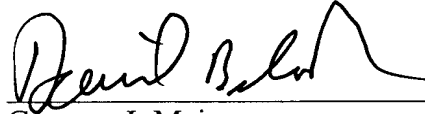
Further, as indicated in the outstanding Office Action, AAPA does not teach or suggest a source electrode and a drain electrode that are surrounded by a semiconductor layer. Accordingly, it is respectfully submitted that AAPA and Hong et al do not teach the features of Claims 1, 3 and 4.

In addition, the specification is amended to correct minor grammatical informalities. The abstract is also amended to better conform with U.S. patent practice. It is believed no new matter is added.

Consequently, in light of the above discussion and in view of the present amendment, this application is believed to be in condition for allowance and an early and favorable action to that effect is respectfully requested.

Respectfully submitted,

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